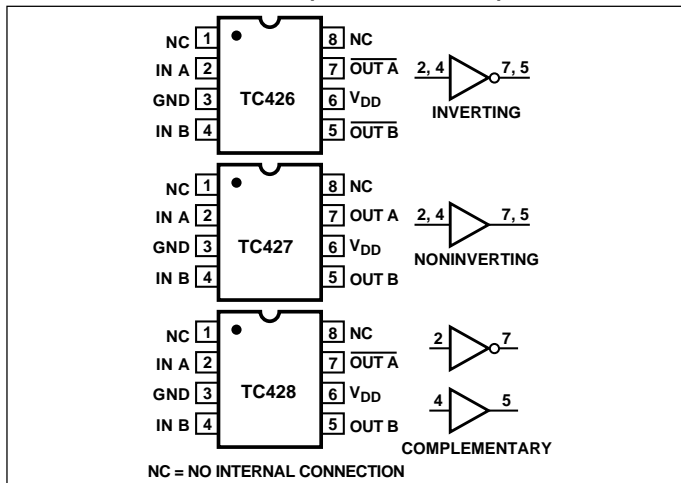**MICROCHIP**

1.5A Dual High-Speed Power Mosfet Drivers
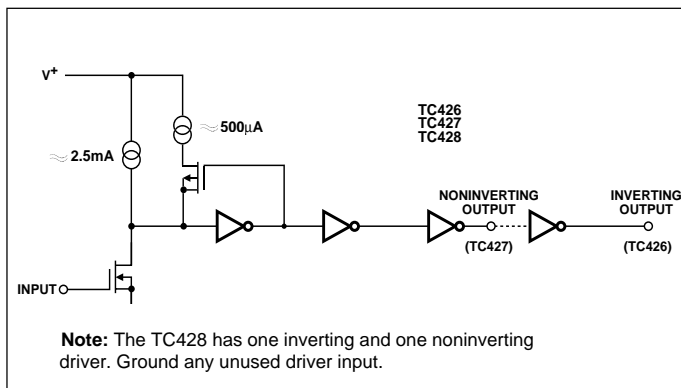
FEATURES

- **High-Speed Switching (C_L = 1000pF)........... 30nsec**
- **High Peak Output Current................................. 1.5A**
- **High Output Voltage Swing .... V_{DD} – 25mV**
  GND +25mV
- **Low Input Current (Logic "0" or "1") 1μA**
- **TTL/CMOS Input Compatible**
- **Available in Inverting and Noninverting Configurations**
- **Wide Operating Supply Voltage .... 4.5V to 18V**
- **Current Consumption**
  — Inputs Low 0.4mA
  — Inputs High 8mA
- **Single Supply Operation**
- **Low Output Impedance 6Ω**
- **Pinout Equivalent of DS0026 and MMH0026**
- **Latch-Up Resistant: Withstands > 500mA Reverse Current**
- **ESD Protected 2kV**

PIN CONFIGURATIONS **(DIP AND SOIC)**

NC = NO INTERNAL CONNECTION

FUNCTIONAL BLOCK DIAGRAM

Note: The TC428 has one inverting and one noninverting driver. Ground any unused driver input.

GENERAL DESCRIPTION

The TC426/TC427/TC428 are dual CMOS high-speed drivers. A TTL/CMOS input voltage level is translated into a rail-to-rail output voltage level swing. The CMOS output is within 25mV of ground or positive supply.

The low impedance, high-current driver outputs swing a 1000pF load 18V in 30nsec. The unique current and voltage drive qualities make the TC426/TC427/TC428 ideal power MOSFET drivers, line drivers, and DC-to-DC converter building blocks.

Input logic signals may equal the power supply voltage. Input current is a low 1μA, making direct interface to CMOS/bipolar switch-mode power supply control ICs possible, as well as open-collector analog comparators.

Quiescent power supply current is 8mA maximum. The TC426 requires 1/5 the current of the pin-compatible bipolar DS0026 device. This is important in DC-to-DC converter applications with power efficiency constraints and high-frequency switch-mode power supply applications. Quiescent current is typically 6mA when driving a 1000pF load 18V at 100kHz.

The inverting TC426 driver is pin-compatible with the bipolar DS0026 and MMH0026 devices. The TC427 is noninverting; the TC428 contains an inverting and non-inverting driver.

Other pin compatible driver families are the TC1426/27/28, TC4426/27/28, and TC4426A/27A/28A.

ORDERING INFORMATION

Part No.	Package	Configuration	Temperature Range
TC426COA	8-Pin SOIC	Inverting	0°C to +70°C
TC426CPA	8-Pin PDIP	Inverting	0°C to +70°C
TC426EOA	8-Pin SOIC	Inverting	–40°C to +85°C
TC426EPA	8-Pin SOIC	Complementary	–40°C to +85°C
TC426IJA	8-Pin CerDIP	Inverting	–25°C to +85°C
TC426MJA	8-Pin CerDIP	Inverting	–55°C to +125°C
TC427COA	8-Pin SOIC	Noninverting	0°C to +70°C
TC427CPA	8-Pin PDIP	Noninverting	0°C to +70°C
TC427EOA	8-Pin SOIC	Noninverting	–40°C to +85°C
TC427EPA	8-Pin SOIC	Complementary	–40°C to +85°C
TC427IJA	8-Pin CerDIP	Noninverting	–25°C to +85°C
TC427MJA	8-Pin CerDIP	Noninverting	–55°C to +125°C
TC428COA	8-Pin SOIC	Complementary	0°C to +70°C
TC428CPA	8-Pin PDIP	Complementary	0°C to +70°C
TC428EOA	8-Pin SOIC	Complementary	–40°C to +85°C
TC428EPA	8-Pin SOIC	Complementary	–40°C to +85°C
TC428IJA	8-Pin CerDIP	Complementary	–25°C to +85°C
TC428MJA	8-Pin CerDIP	Complementary	–55°C to +125°C

1.5A Dual High-Speed Power Mosfet Drivers

ABSOLUTE MAXIMUM RATINGS*

Supply Voltage .... +20V
Input Voltage, Any Terminal .... V_{DD} + 0.3V to GND – 0.3V
Power Dissipation ($T_A \leq 70°C$)
    Plastic 730mW
    CerDIP 800mW
    SOIC 470mW
Derating Factor
    Plastic .... 8mW/°C

    CerDIP .... 6.4mW/°C
    SOIC .... 4mW/°C
Operating Temperature Range
    C Version .... 0°C to +70°C
    .... I Version
    – 25°C to +85°C
    E Version .... – 40°C to +85°C
    M Version .... – 55°C to +125°C
Maximum Chip Temperature .... +150°C
Storage Temperature Range .... – 65°C to +150°C
Lead Temperature (Soldering, 10 sec) .... +300°C

ELECTRICAL CHARACTERISTICS: T_A = +25°C with 4.5V $\leq V_{DD} \leq$ 18V, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Input						
V_{IH}	Logic 1, High Input Voltage		2.4	—	—	V
V_{IL}	Logic 0, Low Input Voltage		—	—	0.8	V
I_{IN}	Input Current	$0V \leq V_{IN} \leq V_{DD}$	−1	—	1	µA
Output						
V_{OH}	High Output Voltage		$V_{DD} - 0.025$	—	—	V
V_{OL}	Low Output Voltage		—	—	0.025	V
R_{OH}	High Output Resistance	I_{OUT} = 10mA, V_{DD} = 18V	—	10	15	Ω
R_{OL}	Low Output Resistance	I_{OUT} = 10mA, V_{DD} = 18V	—	6	10	Ω
I_{PK}	Peak Output Current		—	1.5	—	A
Switching Time (Note 1)						
t_R	Rise Time	Test Figure 1/2	—	—	30	nsec
t_F	Fall Time	Test Figure 1/2	—	—	30	nsec
t_{D1}	Delay Time	Test Figure 1/2	—	—	50	nsec
t_{D2}	Delay Time	Test Figure 1/2	—	—	75	nsec
Power Supply						
I_S	Power Supply Current	V_{IN} = 3V (Both Inputs)	—	—	8	mA
		V_{IN} = 0V (Both Inputs)	—	—	0.4	mA

ELECTRICAL CHARACTERISTICS: Over Operating Temperature Range with 4.5V $\leq V_{DD} \leq$ 18V, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Input						
V_{IH}	Logic 1, High Input Voltage		2.4	—	—	V
V_{IL}	Logic 0, Low Input Voltage		—	—	0.8	V
I_{IN}	Input Current	$0V \leq V_{IN} \leq V_{DD}$	−10	—	10	µA
Output						
V_{OH}	High Output Voltage		$V_{DD} - 0.025$	—	—	V
V_{OL}	Low Output Voltage		—	—	0.025	V
R_{OH}	High Output Resistance	I_{OUT} = 10mA, V_{DD} = 18V	—	13	20	Ω
R_{OL}	Low Output Resistance	I_{OUT} = 10mA, V_{DD} = 18V	—	8	15	Ω
Switching Time (Note 1)						
t_R	Rise Time	Test Figure 1/2	—	—	60	nsec
t_F	Fall Time	Test Figure 1/2	—	—	30	nsec
t_{D1}	Delay Time	Test Figure 1/2	—	—	75	nsec
t_{D2}	Delay Time	Test Figure 1/2	—	—	120	nsec
Power Supply						
I_S	Power Supply Current	V_{IN} = 3V (Both Inputs)	—	—	12	mA
		V_{IN} = 0V (Both Inputs)	—	—	0.6	mA

NOTE: 1. Switching times guaranteed by design.

1.5A Dual High-Speed
Power Mosfet Drivers

*Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may effect device reliability.

SUPPLY BYPASSING

Charging and discharging large capacitive loads quickly requires large currents. For example, charging a 1000pF load to 18V in 25nsec requires an 0.72A current from the device power supply.

To guarantee low supply impedance over a wide frequency range, a parallel capacitor combination is recommended for supply bypassing. Low-inductance ceramic disk capacitors with short lead lengths (< 0.5 in.) should be used. A 1μF film capacitor in parallel with one or two 0.1μF ceramic disk capacitors normally provides adequate bypassing.

GROUNDING

The TC426 and TC428 contain inverting drivers. Ground potential drops developed in common ground impedances from input to output will appear as negative feedback and degrade switching speed characteristics.

Individual ground returns for the input and output circuits or a ground plane should be used.

INPUT STAGE

The input voltage level changes the no-load or quiescent supply current. The N-channel MOSFET input stage transistor drives a 2.5mA current source load. With a logic "1" input, the maximum quiescent supply current is 8 mA. Logic "0" input level signals reduce quiescent current to 0.4mA maximum. Minimum power dissipation occurs for logic "0" inputs for the TC426/427/428. **Unused driver inputs must be connected to V$_{DD}$ or GND**.

The drivers are designed with 100mV of hysteresis. This provides clean transitions and minimizes output stage current spiking when changing states. Input voltage thresholds are approximately 1.5V, making the device TTL compatible over the 4.5V to 18V supply operating range. Input current is less than 1μA over this range.

The TC426/427/428 may be directly driven by the TL494, SG1526/1527, SG1524, SE5560, and similar switch-mode power supply integrated circuits.

POWER DISSIPATION

The supply current vs frequency and supply current vs capacitive load characteristic curves will aid in determining power dissipation calculations.

The TC426/427/428 CMOS drivers have greatly reduced quiescent DC power consumption. Maximum quiescent current is 8mA compared to the DS0026 40mA specification. For a 15V supply, power dissipation is typically 40mW.

Two other power dissipation components are:
- Output stage AC and DC load power.
- Transition state power.

Output stage power is:
$$P_o = P_{DC} + PAC$$
$$= V_o (I_{DC}) + f\, C_L\, V_S^2$$

Where:
V_o = DC output voltage
I_{DC} = DC output load current
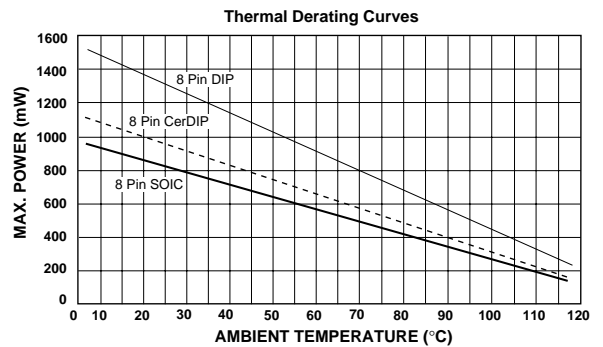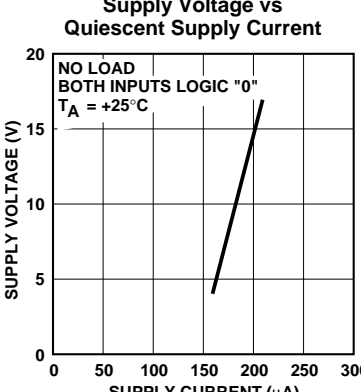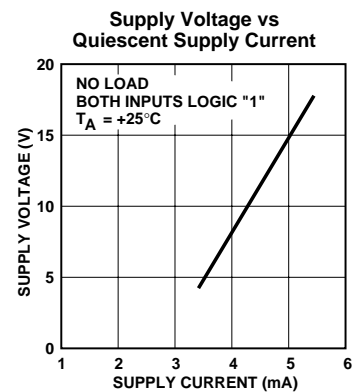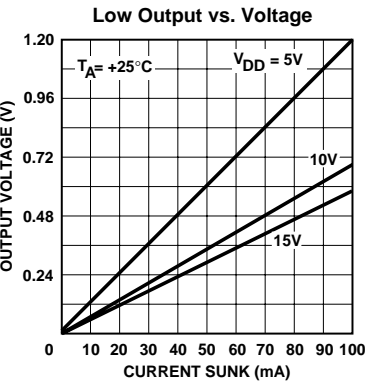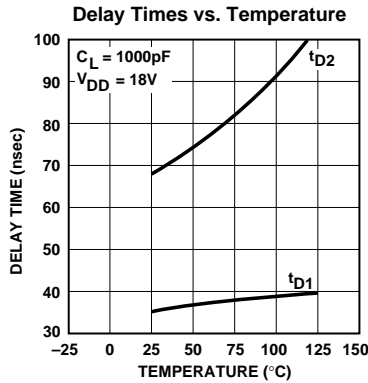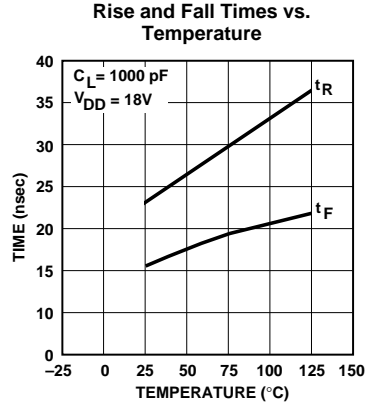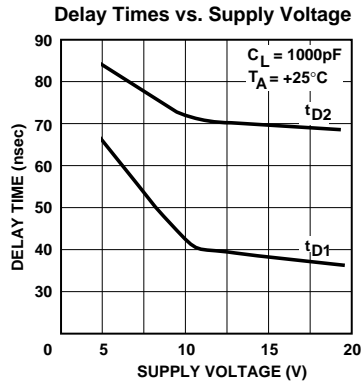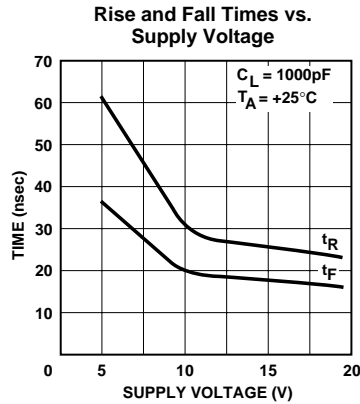f = Switching frequency
V_s = Supply voltage

In power MOSFET drive applications the P$_{DC}$ term is negligible. MOSFET power transistors are high impedance, capacitive input devices. In applications where resistive loads or relays are driven, the P$_{DC}$ component will normally dominate.

The magnitude of P$_{AC}$ is readily estimated for several cases:

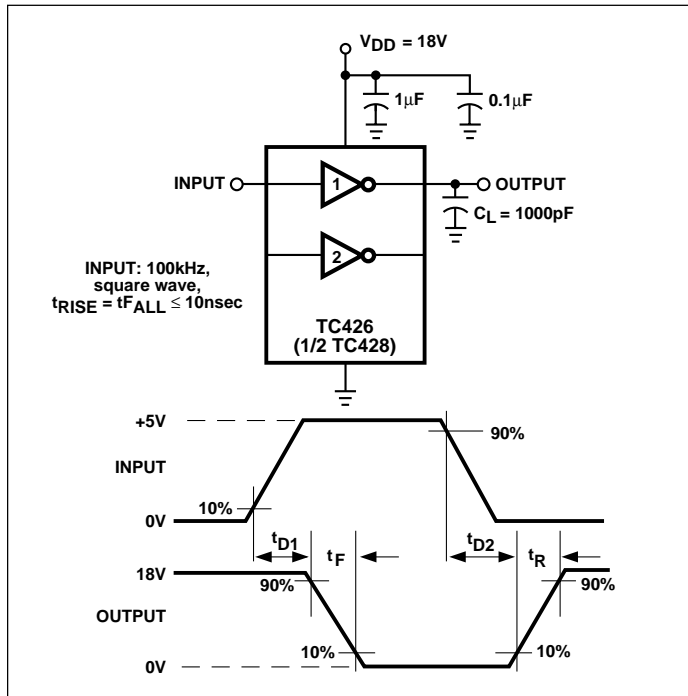| A.	B.
1. f = 200kHZ	1. f = 200kHz
2. C$_L$ =1000pf	2. C$_L$ =1000pf
3. Vs = 18V	3. VS = 15V
4. P$_{AC}$ = 65mW	4. P$_{AC}$ = 45mW

During output level state changes, a current surge will flow through the series connected N and P channel output MOSFETS as one device is turning "ON" while the other is turning "OFF". The current spike flows only during output transitions. The input levels should not be maintained between the logic "0" and logic "1" levels. **Unused driver inputs must be tied to ground and not be allowed to float.** Average power dissipation will be reduced by minimizing input rise times. As shown in the characteristic curves, average supply current is frequency dependent.

TYPICAL CHARACTERISTICS

Rise and Fall Times vs. Supply Voltage

Delay Times vs. Supply Voltage

Rise and Fall Times vs. Temperature

Delay Times vs. Temperature

Supply Current vs. Capacitive Load

Rise and Fall Times vs. Capacitive Load

Supply Current vs. Frequency

High Output vs. Voltage

Low Output vs. Voltage

Supply Voltage vs Quiescent Supply Current

Supply Voltage vs Quiescent Supply Current

Thermal Derating Curves

1.5A Dual High-Speed
Power Mosfet Drivers

Test Figure 1. Inverting Driver Switching Time Test Circuit
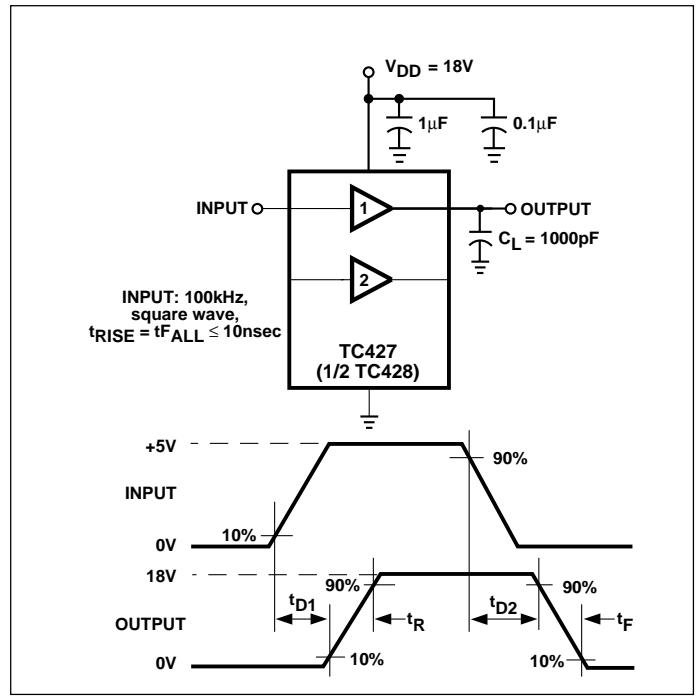
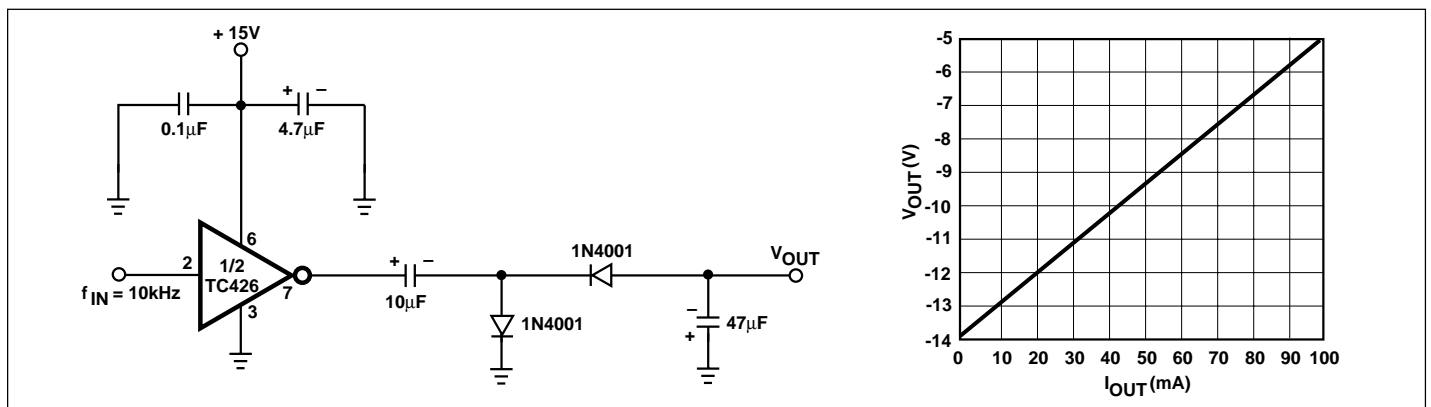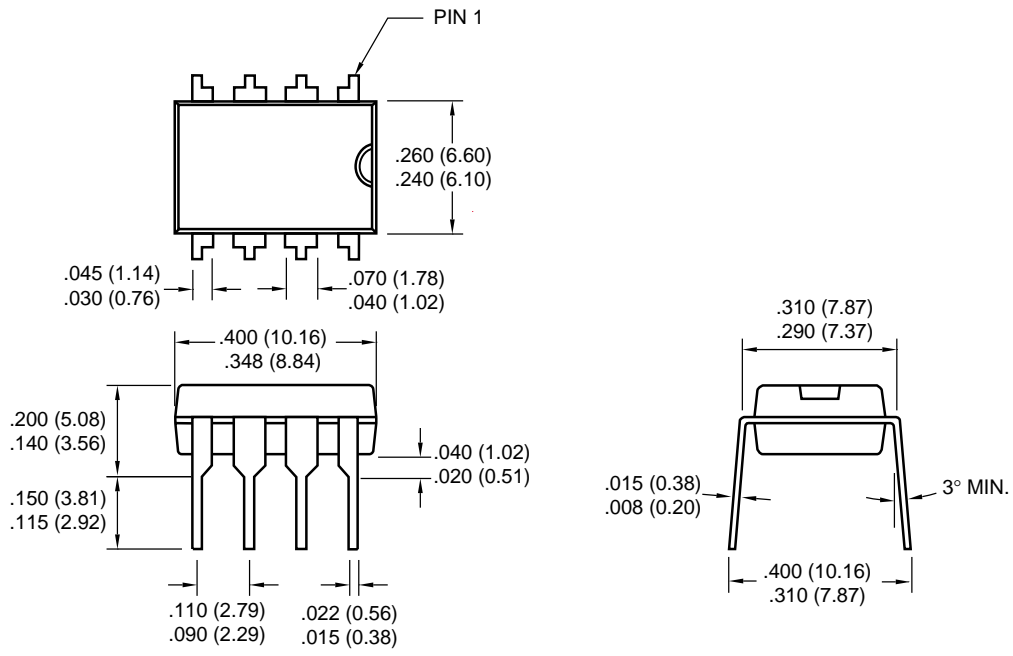**Test Figure 2. Noninverting Driver Switching Time Test Circuit**
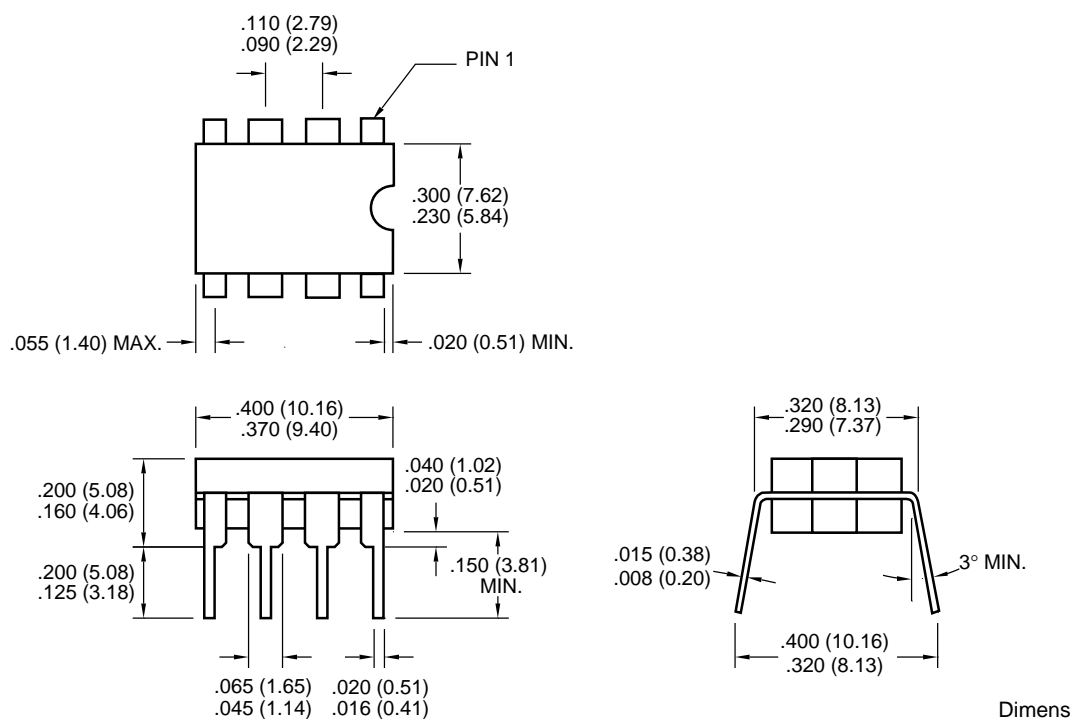
VOLTAGE DOUBLER

VOLTAGE INVERTER

PACKAGE DIMENSIONS

8-Pin PDIP (Narrow)

PIN 1

.260 (6.60)
.240 (6.10)

.045 (1.14)
.030 (0.76)

.070 (1.78)
.040 (1.02)

.400 (10.16)
.348 (8.84)

.200 (5.08)
.140 (3.56)

.040 (1.02)
.020 (0.51)

.150 (3.81)
.115 (2.92)

.110 (2.79)
.090 (2.29)

.022 (0.56)
.015 (0.38)

.310 (7.87)
.290 (7.37)

.015 (0.38)
.008 (0.20)

3° MIN.

.400 (10.16)
.310 (7.87)

8-Pin CDIP (Narrow)

.110 (2.79)
.090 (2.29)

PIN 1

.300 (7.62)
.230 (5.84)

.055 (1.40) MAX.

.020 (0.51) MIN.

.400 (10.16)
.370 (9.40)

.200 (5.08)
.160 (4.06)

.040 (1.02)
.020 (0.51)

.200 (5.08)
.125 (3.18)

.150 (3.81)
MIN.

.065 (1.65)
.045 (1.14)

.020 (0.51)
.016 (0.41)

.320 (8.13)
.290 (7.37)

.015 (0.38)
.008 (0.20)

3° MIN.

.400 (10.16)
.320 (8.13)
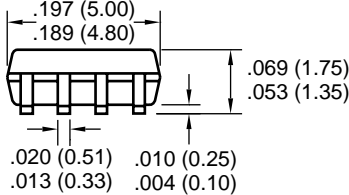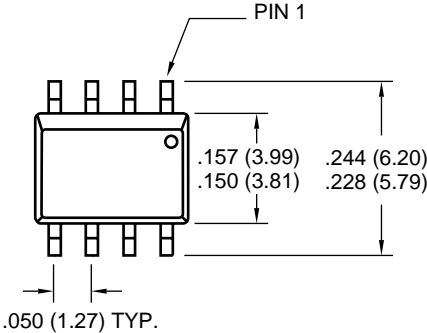
Dimensions: inches (mm)

1.5A Dual High-Speed
Power Mosfet Drivers

TC426
TC427
TC428

PACKAGE DIMENSIONS

8-Pin SOIC (Narrow)

PIN 1

.157 (3.99)
.150 (3.81)

.244 (6.20)
.228 (5.79)

.050 (1.27) TYP.

.197 (5.00)
.189 (4.80)

.069 (1.75)
.053 (1.35)

.020 (0.51)
.013 (0.33)

.010 (0.25)
.004 (0.10)

8° MAX.

.050 (1.27)
.016 (0.40)

.010 (0.25)
.007 (0.18)

Dimensions: inches (mm)

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TC426/7/8-7   12/6/99

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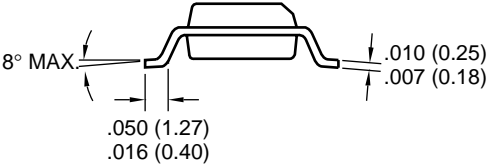
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Dallas
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Addison, TX 75001
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Dayton
Two Prestige Place, Suite 130
Miamisburg, OH 45342
Tel: 937-291-1654 Fax: 937-291-9175

Detroit
Tri-Atria Office Building
32255 Northwestern Highway, Suite 190
Farmington Hills, MI 48334
Tel: 248-538-2250 Fax: 248-538-2260

Los Angeles
18201 Von Karman, Suite 1090
Irvine, CA 92612
Tel: 949-263-1888 Fax: 949-263-1338

Mountain View
Analog Product Sales
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Mountain View, CA 94043-1836
Tel: 650-968-9241 Fax: 650-967-1590

New York
150 Motor Parkway, Suite 202
Hauppauge, NY 11788
Tel: 631-273-5305 Fax: 631-273-5335

San Jose
Microchip Technology Inc.
2107 North First Street, Suite 590
San Jose, CA 95131
Tel: 408-436-7950 Fax: 408-436-7955

Toronto
6285 Northam Drive, Suite 108
Mississauga, Ontario L4V 1X5, Canada
Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

China - Beijing
Microchip Technology Beijing Office
Unit 915
New China Hong Kong Manhattan Bldg.
No. 6 Chaoyangmen Beidajie
Beijing, 100027, No. China
Tel: 86-10-85282100 Fax: 86-10-85282104

China - Shanghai
Microchip Technology Shanghai Office
Room 701, Bldg. B
Far East International Plaza
No. 317 Xian Xia Road
Shanghai, 200051
Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

Hong Kong
Microchip Asia Pacific
RM 2101, Tower 2, Metroplaza
223 Hing Fong Road
Kwai Fong, N.T., Hong Kong
Tel: 852-2401-1200 Fax: 852-2401-3431

India
Microchip Technology Inc.
India Liaison Office
Divyasree Chambers
1 Floor, Wing A (A3/A4)
No. 11, O'Shaugnessey Road
Bangalore, 560 025, India
Tel: 91-80-2290061 Fax: 91-80-2290062

Japan
Microchip Technology Intl. Inc.
Benex S-1 6F
3-18-20, Shinyokohama
Kohoku-Ku, Yokohama-shi
Kanagawa, 222-0033, Japan
Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea
Microchip Technology Korea
168-1, Youngbo Bldg. 3 Floor
Samsung-Dong, Kangnam-Ku
Seoul, Korea
Tel: 82-2-554-7200 Fax: 82-2-558-5934

ASIA/PACIFIC (continued)

Singapore
Microchip Technology Singapore Pte Ltd.
200 Middle Road
#07-02 Prime Centre
Singapore, 188980
Tel: 65-334-8870 Fax: 65-334-8850

Taiwan
Microchip Technology Taiwan
11F-3, No. 207
Tung Hua North Road
Taipei, 105, Taiwan
Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Australia
Microchip Technology Australia Pty Ltd
Suite 22, 41 Rawson Street
Epping 2121, NSW
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Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany
Arizona Microchip Technology GmbH
Gustav-Heinemann Ring 125
D-81739 Munich, Germany
Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

Germany
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Lochhamer Strasse 13
D-82152 Martinsried, Germany
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Italy
Arizona Microchip Technology SRL
Centro Direzionale Colleoni
Palazzo Taurus 1 V. Le Colleoni 1
20041 Agrate Brianza
Milan, Italy
Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom
Arizona Microchip Technology Ltd.
505 Eskdale Road
Winnersh Triangle
Wokingham
Berkshire, England RG41 5TU
Tel: 44 118 921 5869 Fax: 44-118 921-5820

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